BURIED BUTTED CONTACT AND METHOD FOR FABRICATING

ABSTRACT OF THE DISCLOSURE

A buried butted contact and method for its fabrication are provided which includes a substrate (1) having dopants of a first conductivity type and having shallow trench isolation. Dopants (5) of a second conductivity type are located in the bottom of an opening (4) in said substrate (1). Ohmic contact is provided between the dopants in the substrate (1) and the low diffusivity dopants that is located on a side a wall of the opening (4). The contact (7) is a metal silicide, metal and/or metal alloy.

FIG. 2